

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 242820US2RD		SERIAL NO. <u>10/662533</u> New Application	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Yoshiaki SAITO, et al.			
				FILING DATE Herewith		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<u>Je</u>	AA	5,659,499	08/19/97	E. CHEN, et al.			
<u>Je</u>	AB	5,956,267	09/21/99	A. T. HURST, et al.			
<u>Je</u>	AC	5,734,605	03/31/98	X. T. ZHU, et al.			
<u>Je</u>	AD	5,640,343	06/17/97	W. J. GALLAGHER, et al.			
<u>Je</u>	AE	5,940,319	08/17/99	M. DURLAM, et al.			
<u>Je</u>	AF	6,351,408	02/26/2002	S. SCHWARZL, et al.			
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
<u>Je</u>	AO	WO 00/10172	02/24/2000	WIPO (with English Abstract)			X
<u>Je</u>	AP	10-4227	01/06/98	JAPAN (with English Abstract)			X
<u>Je</u>	AQ	WO 99/14760	03/25/99	WIPO (with English Abstract)			X
<u>Je</u>	AR	197 44 095	04/15/99	WIPO (with corr. US 6,351,408)			X
	AS						
	AT						
	AU						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
<u>Je</u>	AV	J. S. MOODERA, et al., "FERROMAGNETIC-INSULATOR-FERROMAGNETIC TUNNELING: SPIN-DEPENDENT TUNNELING AND LARGE MAGNETORESISTANCE IN TRILAYER JUNCTION (INVITED)", Vol. 79, No. 8, pgs. 4724-4729, J. Appl. Phys., April 15, 1996					
<u>Je</u>	AW	L. F. SCHELP, et al., "SPIN-DEPENDENT TUNNELING WITH COULOMB BLOCKADE", Vol. 56, No. 10, pgs. R5747-R5750, Physical Review B, September 1, 1997					
<u>Je</u>	AX	Y. SAITO, et al., "SPIN-DEPENDENT TUNNELING THROUGH LAYERED HARD-MAGNETIC-NANO-PARTICLES", Vol. 23, No. 4-2, pgs. 1269-1272, J. Jpn. Appl. Magn. Society, 1999 (with English Abstract)					
<u>Je</u>	AY	F. MONTAGNE, et al., "ENHANCED TUNNEL MAGNETORESISTANCE AT HIGH BIAS VOLTAGE IN DOUBLE-BARRIER PLANAR JUNCTIONS", Vol. 73, No. 19, pgs. 2829-2831, Applied Physics Letters, November 9, 1998					
<u>Je</u>	AZ	Y. SAITO, et al., "CORRELATION BETWEEN BARRIER WIDTH, BARRIER HEIGHT, AND DC BIAS VOLTAGE DEPENDENCES ON THE MAGNETORESISTANCE RATIO IN Ir-Mn EXCHANGE BIASED SINGLE AND DOUBLE TUNNEL JUNCTIONS", Vol. 39, pgs. L1035-L1038, Jpn. J. Appl. Phys., 2000				<input type="checkbox"/> Additional References sheet(s) attached	
Examiner <u>Vu Le</u>							
Date Considered <u>03/07/04</u>							

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.